## MITSUBISHI SEMICONDUCTOR (GaAs FET)

# **MGF0904A**

L, S BAND POWER GaAs FET

### **DESCRIPTION**

The MGF0904A, GaAs FET with an N-channel schottky gate, is designed for use in UHF band amplifiers.

#### **FEATURES**

High output power

 $P_0 = 28dBm \text{ (TYP.) } @ f = 1.65GHz, P_{in} = 15dBm$ 

• High power gain

 $G_P = 13.0 dB (TYP.) @ f = 1.65 GHz, P_{in} = 15 dBm$ 

• High power added efficiency

 $\eta_{\rm add}$  = 40% (TYP.) @ f = 1.65GHz,  $P_{\rm in}$  = 15dBm

#### **APPLICATION**

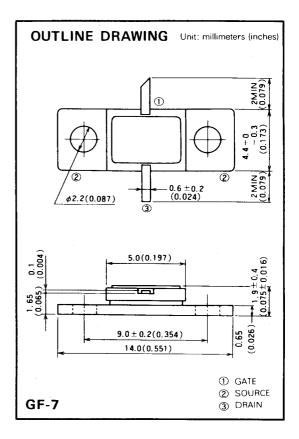
For UHF Band power amplifiers

### **QUALITY GRADE**

• GG

### **RECOMMENDED BIAS CONDITIONS**

- V<sub>DS</sub>=8V
- I<sub>D</sub>=200mA
- Rg=500Ω
- Refer to Bias Procedure



### ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Symbol	Parameter	Ratings	Unit	
V <sub>GSO</sub>	Gate to source voltage	-17	V	
V <sub>GDO</sub>	Gate to drain voltage	-17	V	
ID	Drain current	800	mA	
I <sub>GR</sub>	Reverse gate current	-2.5	mA	
IGF	Forward gate current	5.4	mA	
PT	Total power dissipation *1	3.75	w	
Tch	Channel temperature	175	°C	
Tstg	Storage temperature	-65~+175	-c	

<sup>\*1:</sup> T<sub>C</sub>=25°C

### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

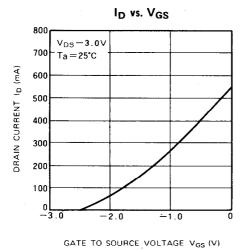
Symbol	Parameter	Test conditions		Units		
	- drameter	rest conditions	Min	Тур	Max	Unit
IDSS	Saturated drain current	$V_{DS} = 3V$ , $V_{GS} = 0V$	400	550	800	mΑ
V <sub>GS(off)</sub>	Gate to source cut-off voltage	V <sub>DS</sub> =3V, I <sub>D</sub> =2.5mA	-1	-3	5	V
9 m	Transconductance	$V_{DS} = 3V$ , $I_D = 300 \text{ mA}$	120	200	_	mS
Po	Output power	V <sub>DS</sub> = 8V, I <sub>D</sub> = 200mA, f = 1.65GHz, P <sub>ID</sub> = 15dBm		28		dBm
$\eta_{add}$	Power added efficiency	VDS - 6 V , 10 - 200111A, 1 - 1.03 GHZ , FIN - 13 GBIII	_	40	_	%
Rth (ch-c)	Thermal resistance * 1	$\Delta V_{f}$ method	_	_	40	°C/W
Rth(ch-a)	Thermal resistance (channel to ambient temperature)	ΔV <sub>f</sub> method	_	_	100	°C\W

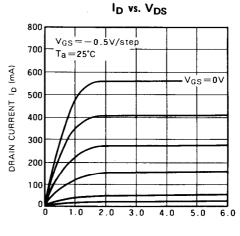
<sup>\*1:</sup> Channel to case

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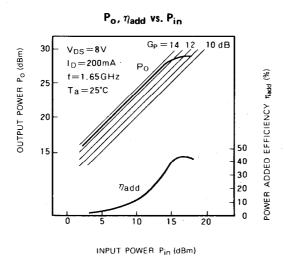
### L, S BAND POWER GaAs FET

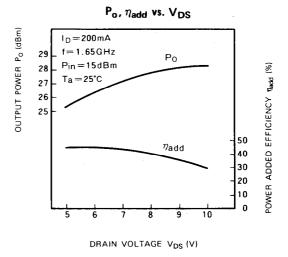
## TYPICAL CHARACTERISTICS





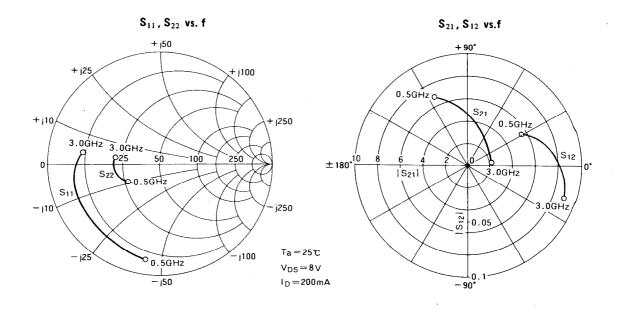
DRAIN TO SOURCE VOLTAGE VDS (V)





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## S PARAMETERS ( $T_a = 25$ °C, $V_{DS} = 8V$ , $I_D = 200$ mA)

f (GHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>		К	MSG/MAG
	Magn.	Angle (deg.)		dΒ						
0.5	0.851	- 99.0	6.855	116.0	0.055	31.0	0.338	-149.0	0.277	21.0
1.0	0.801	-138.0	4.265	89.0	0.064	22.5	0.368	-162.0	0.521	18.2
1.5	0.788	-161.5	3.192	71.0	0.072	13.0	0.390	-173.3	0.655	16.5
2.0	0.740	-177.0	2.544	52.0	0.079	4.0	0.409	-178.0	0.847	15.1
2.5	0.713	176.5	2.180	30.0	0.085	- 7.0	0.411	177.0	0.940	14.1
3.0	0.670	171.5	2.040	9.0	0.091	-18.0	0.402	172.0	1.070	11.9

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